

ABSTRACT OF THE DISCLOSURE

There is disclosed a silicon focus ring consisting of silicon single crystal used as a silicon focus ring in a plasma apparatus, wherein concentration of interstitial oxygen contained in the silicon focus ring is not less than 5×10^{17} atoms/cm³ and not more than 1.5×10^{18} atoms/cm³, and a producing method for a silicon focus ring used for a plasma apparatus, wherein a single crystal silicon wherein concentration of interstitial oxygen contained in the silicon focus ring is not less than 5×10^{17} atoms/cm³ and not more than 1.5×10^{18} atoms/cm³ is grown by a Czochralski method, the single crystal silicon is processed in a circle, and a silicon focus ring is produced. There can be provided a silicon focus ring, which can prevent disadvantage due to impurities such as heavy metal.